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Docket No.: M4065.0536/P536-B  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of:  
Hongmei Wang et al.

Application No.: 10/751,443

Confirmation No.: 2565

Filed: January 6, 2004

Art Unit: 2814

For: FULLY-DEPLETED (FD) (SOI) MOSFET  
ACCESS TRANSISTOR (AS AMENDED)

Examiner: C. M. D. Pizarro

**AMENDMENT IN RESPONSE TO NON-FINAL OFFICE ACTION**

MS Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

**INTRODUCTORY COMMENTS**

In response to the Office Action dated March 21, 2005 (Paper No. 0305),  
please amend the above-identified U.S. patent application as follows:

**Amendments to the Specification** begin on page 2 of this paper.

**Amendments to the Claims** are reflected in the listing of claims which begins  
on page 3 of this paper.

**Remarks** begin on page 5 of this paper.